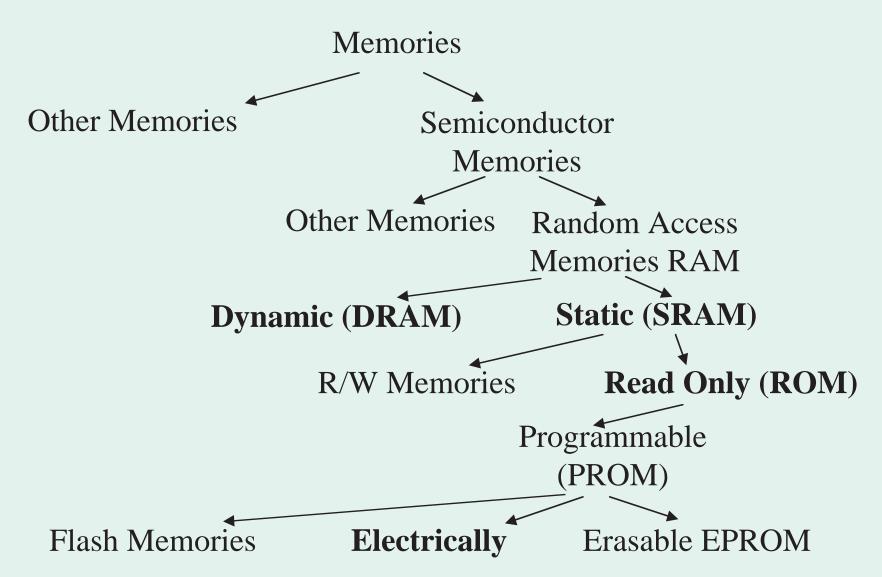
18 - 322

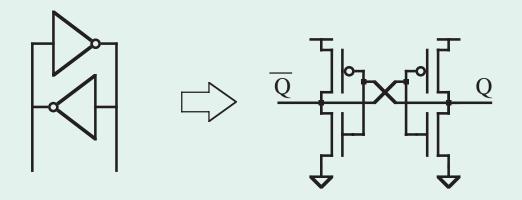
Fall '02 Lecture 24a Static Random Access

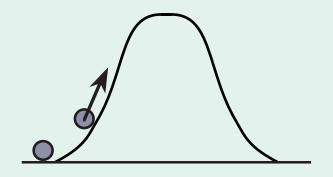
- Memory Classification
- CMOS static memory
 - Six transistor memory cell
 - Memory architecture
 - Decoders
 - Read/Write circuitry
- RMOS static memory
 - Four transistor memory cell
 - Technology
 - Memory cell layout

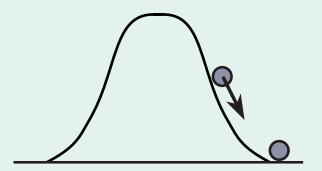
Memory Classification



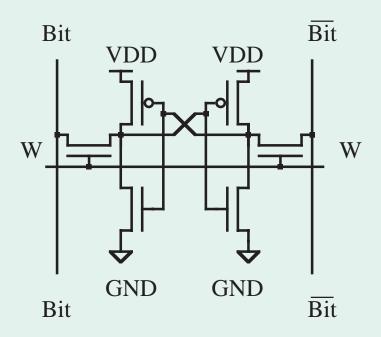
Six transistor memory cell

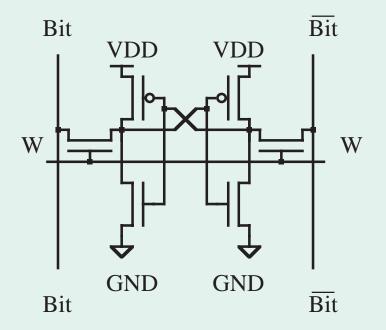


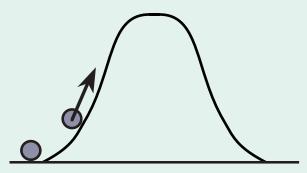


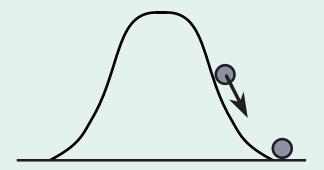


Six transistor memory cell

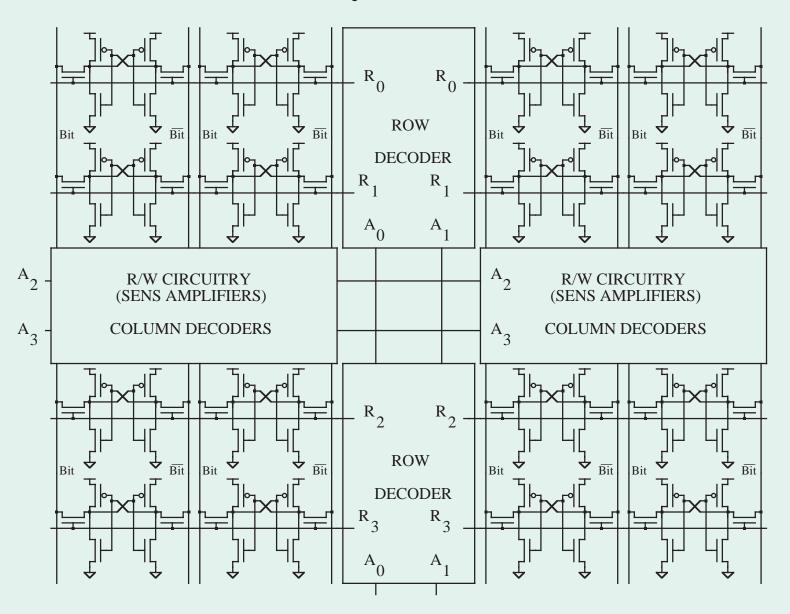




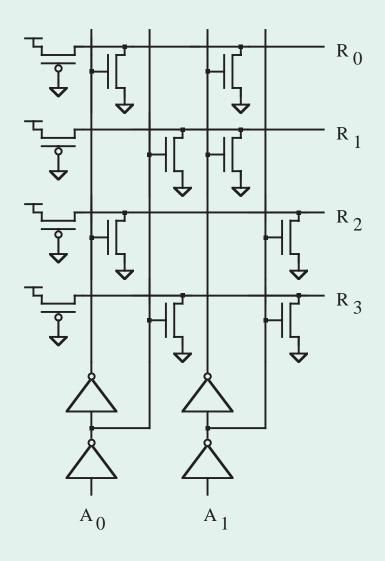


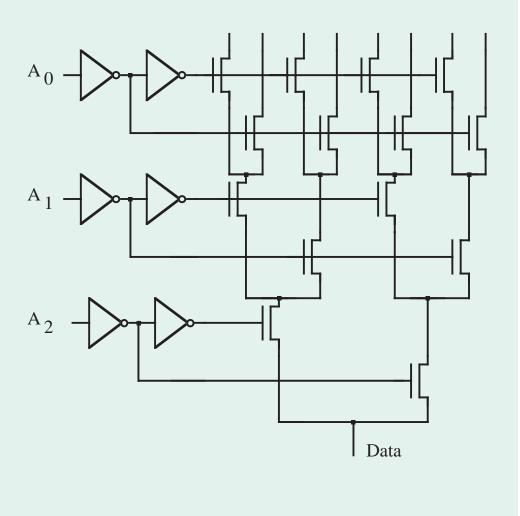


Memory architecture

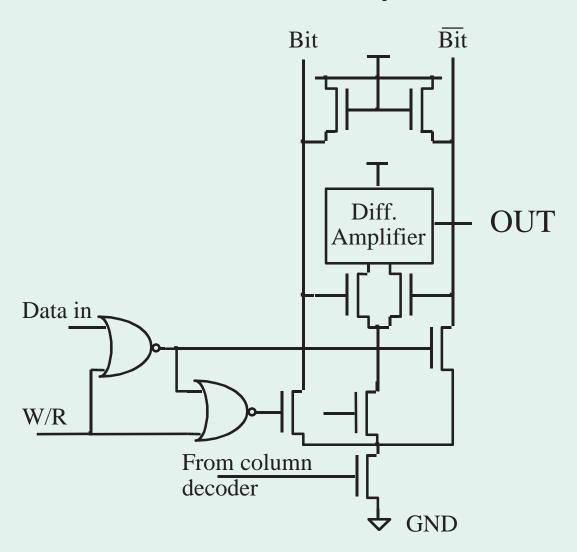


Decoders

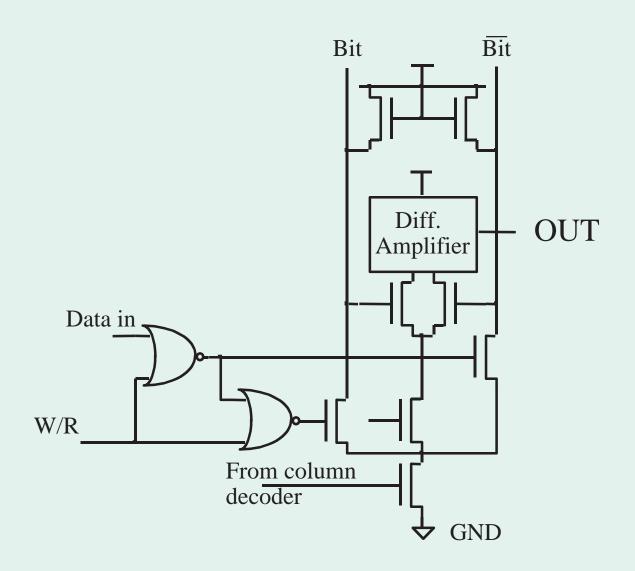




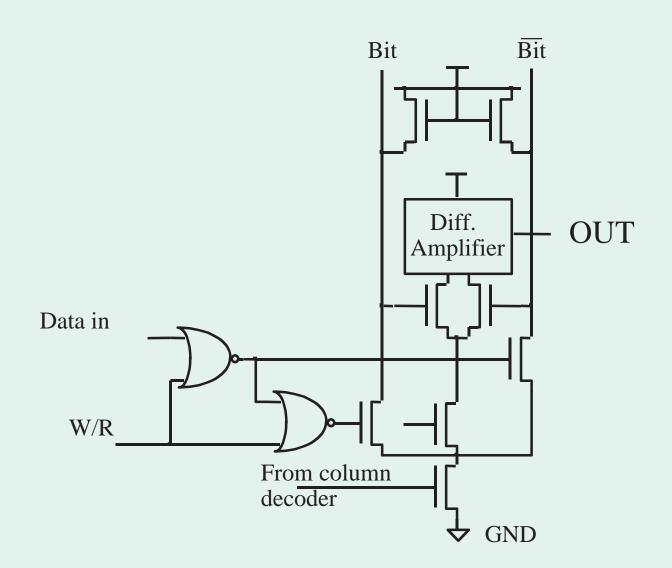
Read/Write circuitry



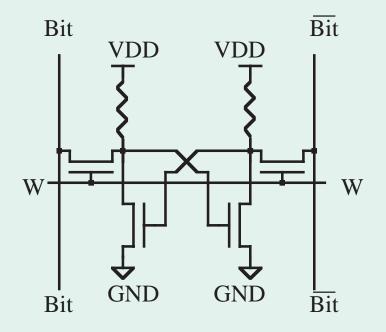
CMOS static memory Read

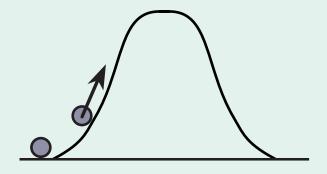


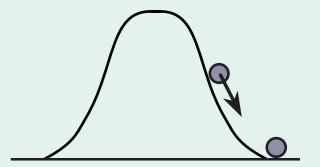
CMOS static memory Write

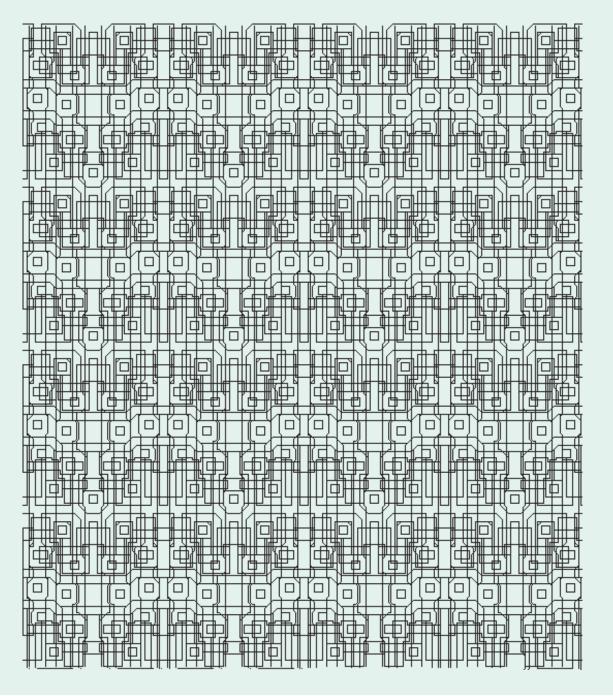


Four transistor memory cell

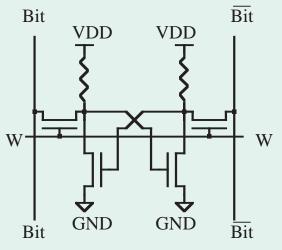




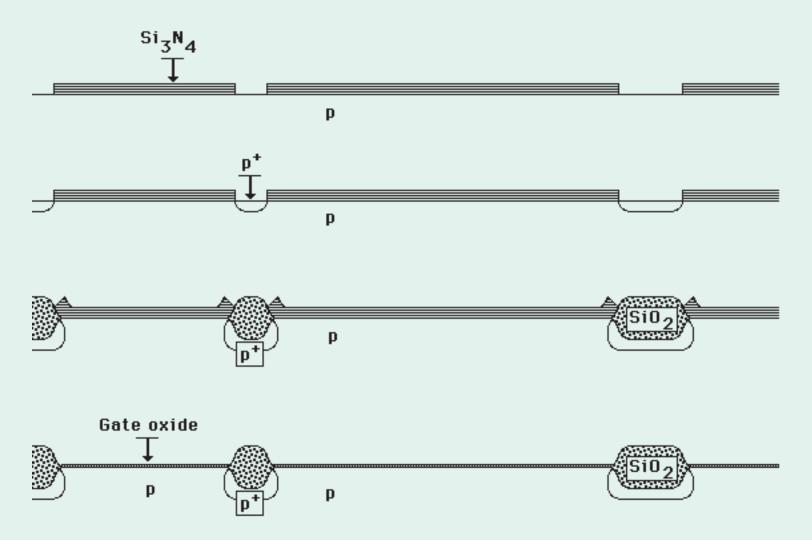


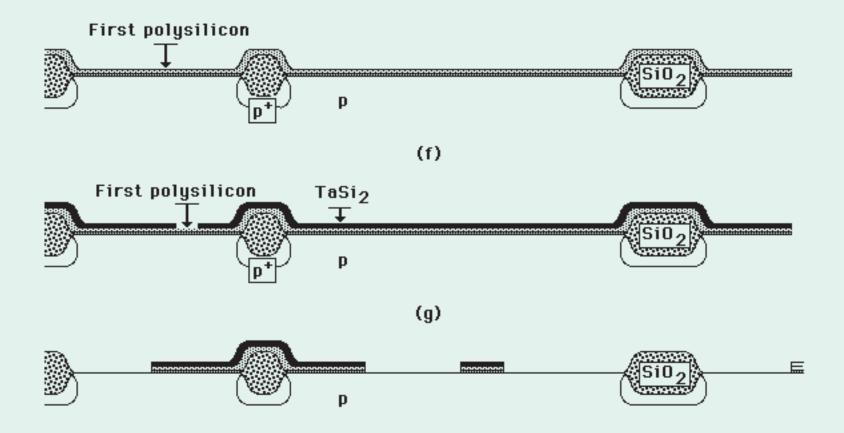


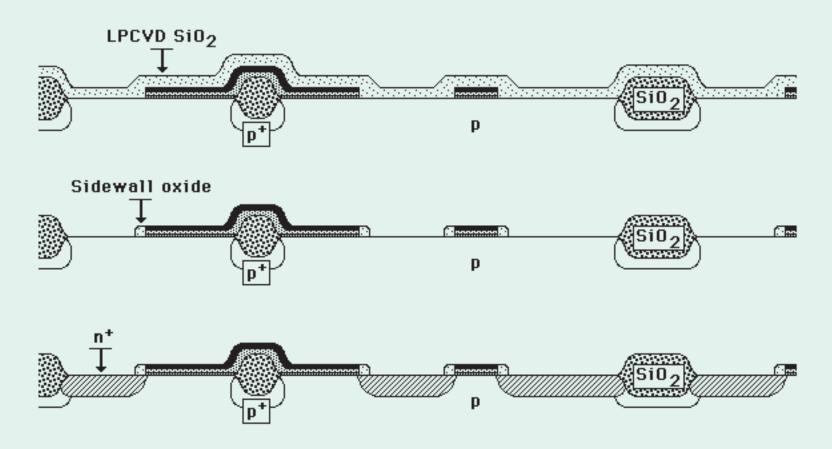
RMOS static memory Technology

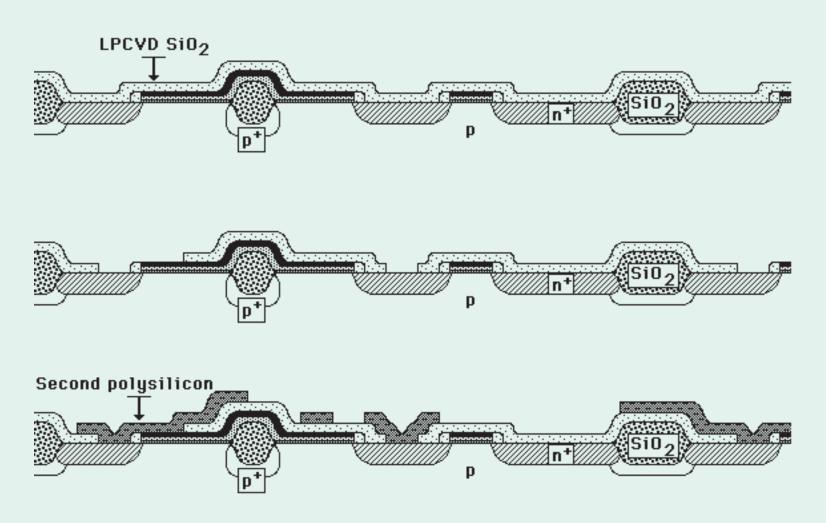


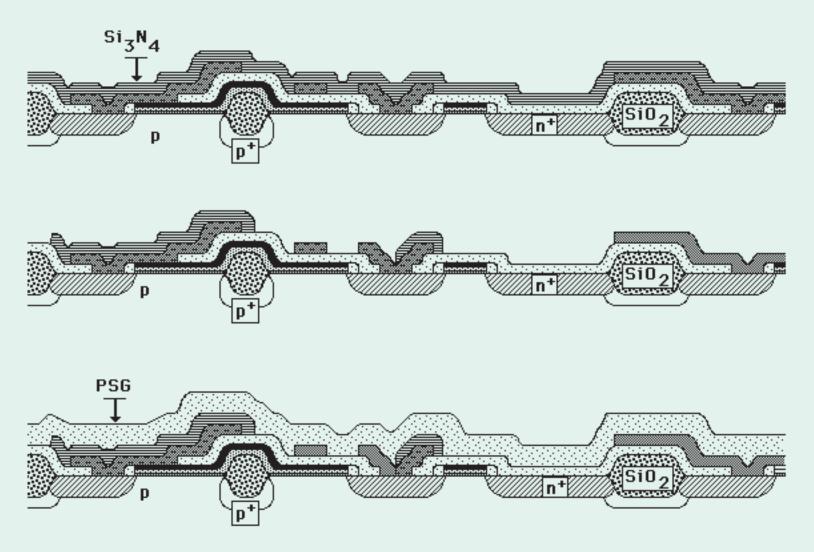
x 128

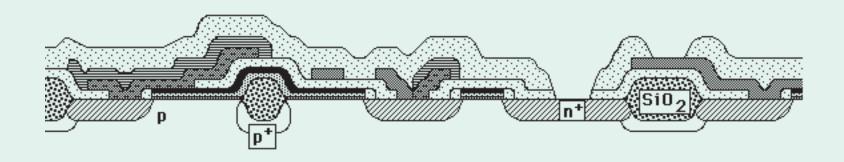


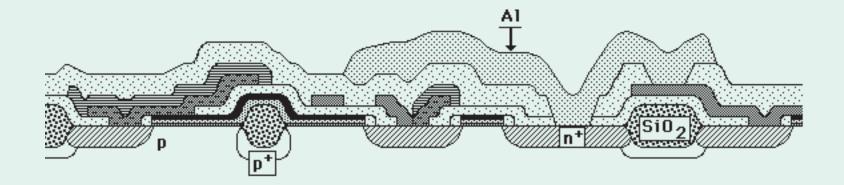




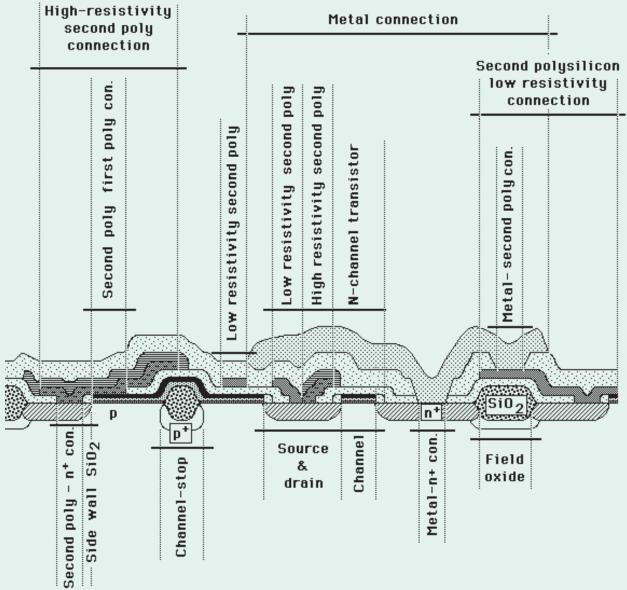


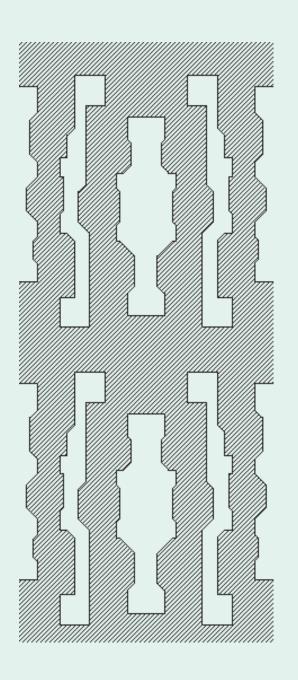




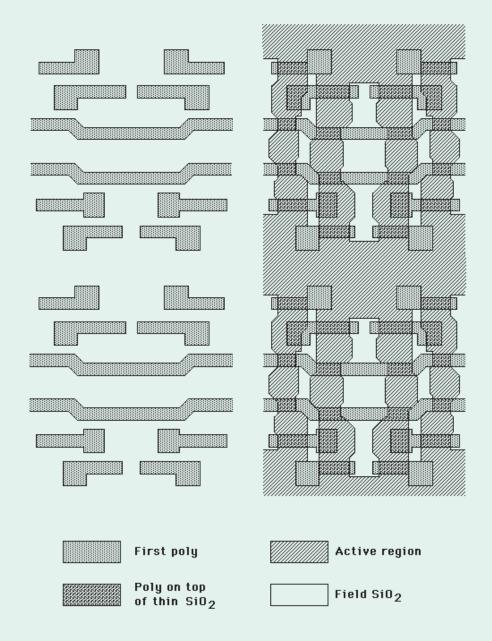


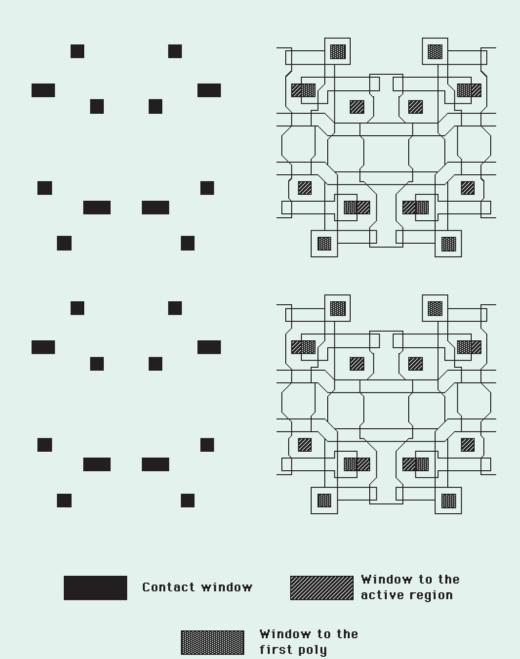
RMOS static memory Technology





Active region Field SiO₂

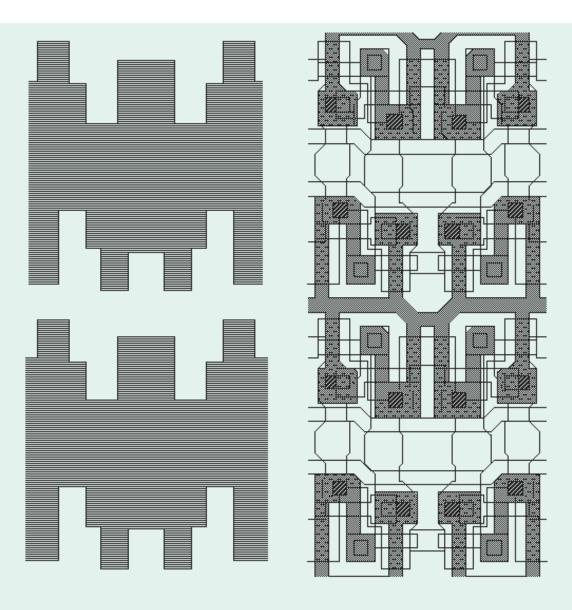




Contact between first First poly and second poly Contact between second Second poly poly and n+ region

Second poly on top of first poly

RMOS static memory Cell layout





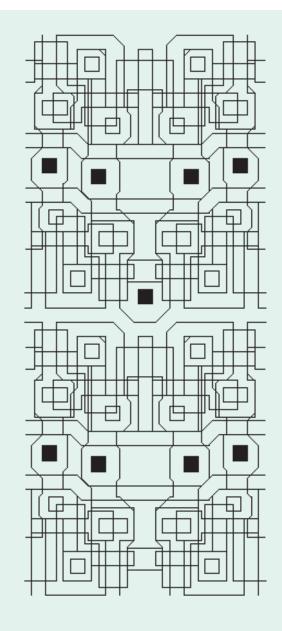


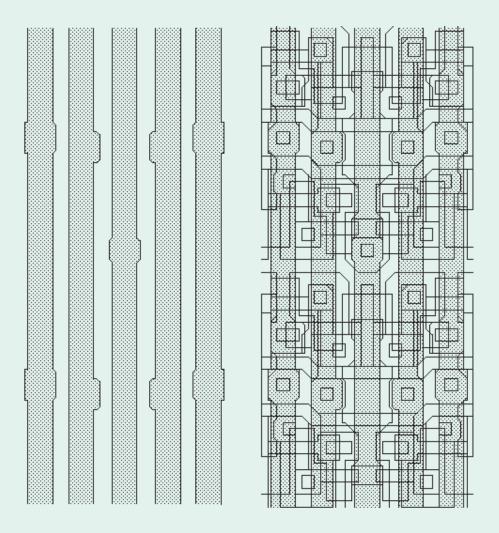


High resistivity second poly



Contact between second poly and n+ region





Metal

Bit line i+1 Word line j Word line j Word line j+1 Word line j+1 Single bit cell V_{cc} Word line j+3 Word line j+3 Word line j+4 Word line j+4

RMOS static memory Cell layout

